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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

N-channel TrenchMOS[™] transistor Logic level FET

FEATURES

- 'Trench' technology
- Extremely fast switching
- Logic level compatible

Subminiature surface mounting package

GENERAL DESCRIPTION

N-channel enhancement mode field-effect transistor in a plastic envelope using 'trench' technology.

Applications:-

- Relay driver
- High-speed line driver
- Telephone ringer

The BSS123 is supplied in the SOT23 subminiature surface mounting package.

LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DSS}	Drain-source voltage	$T_i = 25 \degree C$ to $150\degree C$	-	100	V
V _{DGR}	Drain-gate voltage	$T_{i} = 25 \text{ °C to } 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	Gate-source voltage		-	± 20	V
I _D	Continuous drain current	$T_a = 25 \degree C$	-	150	mA
I _{DM}	Pulsed drain current	$T_a = 25 \degree C$	-	600	mA
P _D	Total power dissipation	T _a = 25 °C	-	0.25	W
T _j , T _{stg}	Operating junction and storage temperature	- -	- 55	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
R _{th j-a}	Thermal resistance junction to ambient	surface mounted on FR4 board	500	-	K/W

PINNING PIN DESCRIPTION 1 gate 2 source

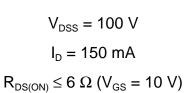
d

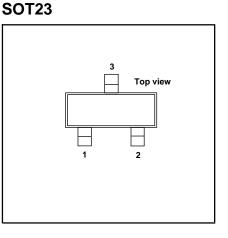
drain

3

SYMBOL

QUICK REFERENCE DATA





N-channel TrenchMOS[™] transistor Logic level FET

BSS123

ELECTRICAL CHARACTERISTICS

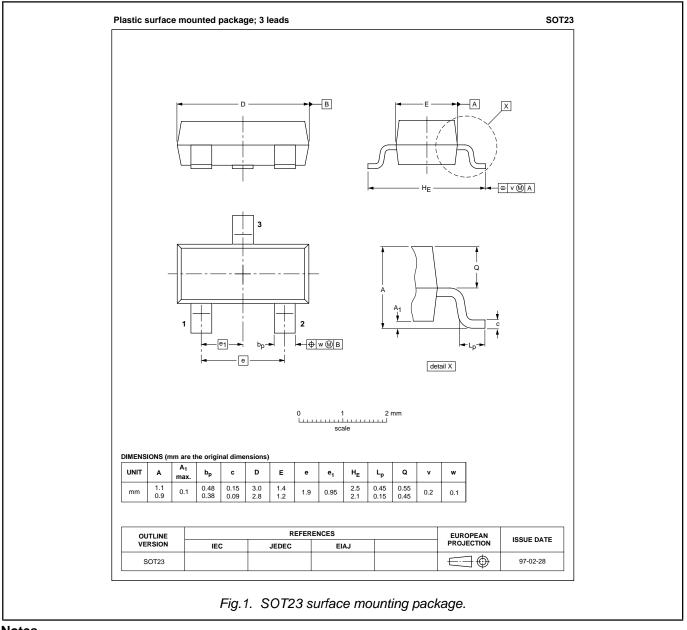
 $T_i = 25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{(BR)DSS}	Drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; \text{ I}_{D} = 10 \mu\text{A}$	100	130	-	V
$\begin{array}{c} V_{GS(TO)} \\ R_{DS(ON)} \end{array}$	Gate threshold voltage Drain-source on-state resistance	$V_{DS} = V_{GS}; I_D = 1 \text{ mA}$ $V_{GS} = 10 \text{ V}; I_D = 120 \text{ mA}$	1 -	2 3.5	2.8 6	V Ω
g _{fs}	Forward transconductance	V _{DS} = 25 V; I _D = 120 mA	-	350	-	mS
I _{DSS}	Zero gate voltage drain current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$	-	10	100	nA
I _{GSS}	Gate source leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nA
t _{on}	Turn-on time	$V_{DD} = 50 \text{ V}; \text{ R}_{D} = 250 \Omega; \text{ V}_{GS} = 10 \text{ V};$ $\text{R}_{G} = 50 \Omega; \text{ Resistive load}$	-	3	10	ns
t _{off}	Turn-off time		-	12	20	ns
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Feedback capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz$	- - -	23 6 4	40 25 10	pF pF pF

BSS123

N-channel TrenchMOS[™] transistor Logic level FET

MECHANICAL DATA



Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.

- 2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
- 3. Epoxy meets UL94 V0 at 1/8".

N-channel TrenchMOS[™] transistor Logic level FET

DEFINITIONS

Data sheet status			
Objective specification	ve specification This data sheet contains target or goal specifications for product development.		
Preliminary specification	ary specification This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.			
Application information			
Where application information is given, it is advisory and does not form part of the specification.			
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